

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of:

Christopher Boguslaw Kocon

Application No.:

Filed: HEREWITH

For: METHOD FOR FORMING A  
SEMICONDUCTOR STRUCTURE WITH  
IMPROVED SMALLER FORWARD  
VOLTAGE LOSS AND HIGHER  
BLOCKING CAPABILITY (as amended)

Customer No.: 20350

Confirmation No.:

Examiner:

Technology Center/Art Unit:

PRELIMINARY AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

September 18, 2003

Sir:

Prior to examination of the above-referenced application, please enter the following amendments and remarks:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 3 of this paper.

**Remarks/Arguments** begin on page 5 of this paper.